

# 2SK2202

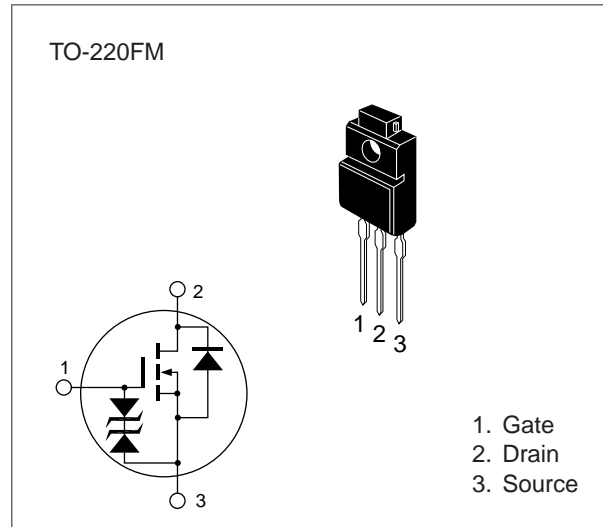
## Silicon N Channel MOS FET

### Application

High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for Switching regulator, DC – DC converter



**Table 1 Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	120	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	7	A
Drain peak current	I <sub>D(pulse)</sub> *	14	A
Body-drain diode reverse drain current	I <sub>DR</sub>	7	A
Channel dissipation	P <sub>ch</sub> **	20	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 μs, duty cycle ≤ 1 %

\*\* Value at T<sub>c</sub> = 25 °C

**Table 2 Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	120	—	—	V	$I_D = 10\text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100\text{ }\mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16\text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	$\mu\text{A}$	$V_{DS} = 100\text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1\text{ mA}$ , $V_{DS} = 10\text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.3	0.4	$\Omega$	$I_D = 4\text{ A}$ $V_{GS} = 10\text{ V}^*$
		—	0.35	0.55	$\Omega$	$I_D = 4\text{ A}$ $V_{GS} = 4\text{ V}^*$
Forward transfer admittance	$ y_{fs} $	3.0	5.0	—	S	$I_D = 4\text{ A}$ $V_{DS} = 10\text{ V}^*$
Input capacitance	$C_{iss}$	—	420	—	pF	$V_{DS} = 10\text{ V}$
Output capacitance	$C_{oss}$	—	140	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	35	—	pF	$f = 1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	9	—	ns	$I_D = 4\text{ A}$
Rise time	$t_r$	—	50	—	ns	$V_{GS} = 10\text{ V}$
Turn-off delay time	$t_{d(off)}$	—	140	—	ns	$R_L = 7.5\text{ }\Omega$
Fall time	$t_f$	—	65	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	1.35	—	V	$I_F = 7\text{ A}$ , $V_{GS} = 0$
Body-drain diode reverse recovery time	$t_{rr}$	—	320	—	ns	$I_F = 7\text{ A}$ , $V_{GS} = 0$ , $di_F / dt = 50\text{ A} / \mu\text{s}$

\* Pulse Test

